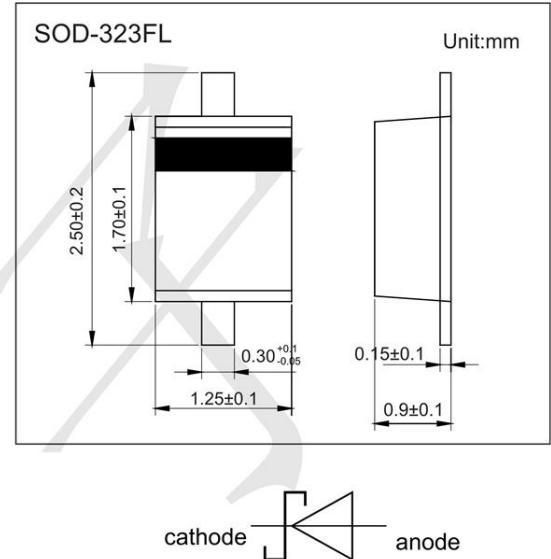


## Features

- Low forward voltage
- Reverse voltage  $V_R \leq 100$  V
- Low capacitance
- High-speed switching
- Very small and flat lead SMD plastic package



### Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Reverse Voltage	$V_{RM}$	100	V
Forward Current	$I_F$	250	mA
Non-Repetitive Peak Forward Current	$I_{FSM}$	2.5	A
Power Dissipation (Note.1) (Note.2)	$P_d$	400	mW
		715	
Thermal Resistance Junction to Ambient (Note.1) (Note.2)	$R_{\theta JA}$	310	°C/W
		175	
Thermal Resistance Junction to Solder Point	$R_{\theta JSP}$	35	
Junction Temperature	$T_J$	150	
Storage Temperature range	$T_{stg}$	-65 to 150	

Note.1:Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

Note.2:Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>3</sup>.

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	$V_R$	$I_R = 100 \mu\text{A}$	100			V
Forward voltage	$V_F$	$I_F = 0.1 \text{ mA}$			200	mV
		$I_F = 10 \text{ mA}$			350	
		$I_F = 10 \text{ mA}, T_J = -40^\circ\text{C}$			470	
		$I_F = 50 \text{ mA}$			475	
		$I_F = 50 \text{ mA}, T_J = -40^\circ\text{C}$			560	
		$I_F = 250 \text{ mA}$			850	
Reverse voltage leakage current	$I_R$	$V_R = 1.5 \text{ V}$			0.5	uA
		$V_R = 1.5 \text{ V}, T_J = 60^\circ\text{C}$			12	
		$V_R = 10 \text{ V}$			0.8	
		$V_R = 10 \text{ V}, T_J = 60^\circ\text{C}$			20	
		$V_R = 50 \text{ V}$			2	
		$V_R = 50 \text{ V}, T_J = 60^\circ\text{C}$			44	
		$V_R = 75 \text{ V}$			4	
		$V_R = 75 \text{ V}, T_J = 60^\circ\text{C}$			80	
		$V_R = 100 \text{ V}$			9	
		$V_R = 100 \text{ V}, T_J = 60^\circ\text{C}$			120	
Junction capacitance	$C_J$	$V_R = 0 \text{ V}, f = 1 \text{ MHz}$			39	pF
		$V_R = 1 \text{ V}, f = 1 \text{ MHz}$			21	
Reverse recovery time	$t_{rr}$	$I_F = I_R = 10 \text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100\Omega$			5.9	ns

**PROTECTION PRODUCTS**  
Typical characteristics

[www.sot23.com.tw](http://www.sot23.com.tw)

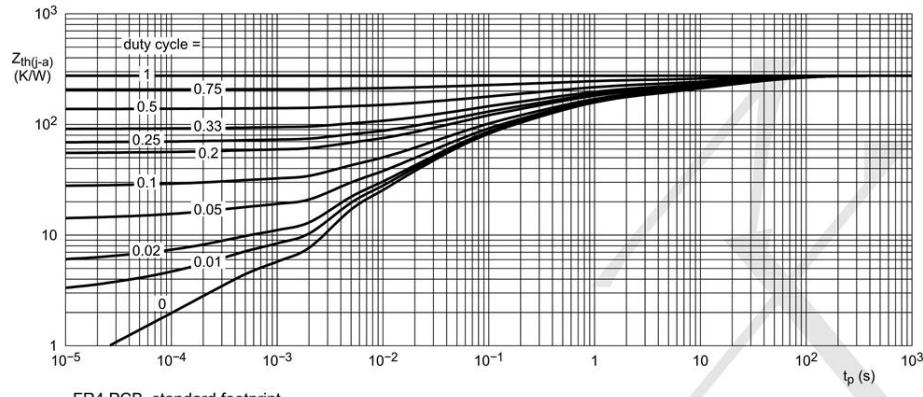


Fig 1. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

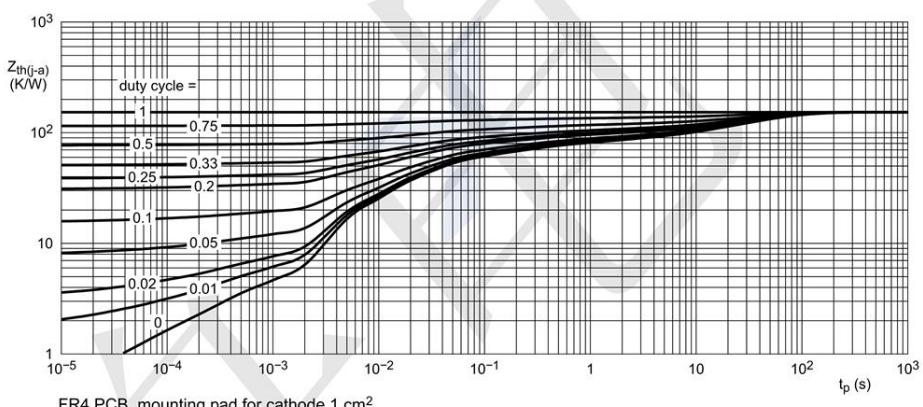


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

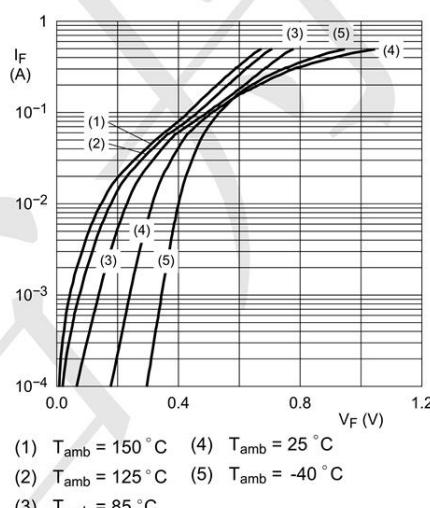


Fig 3. Forward current as a function of forward voltage; typical values

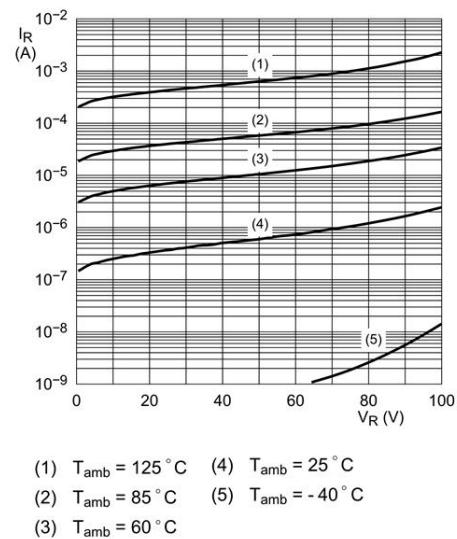
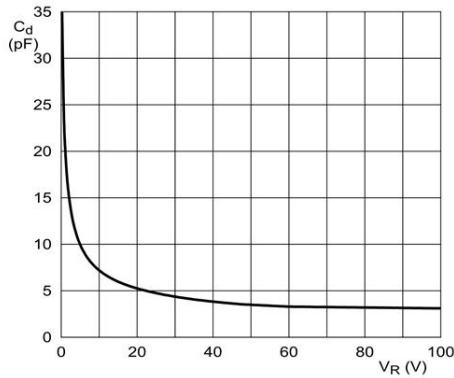


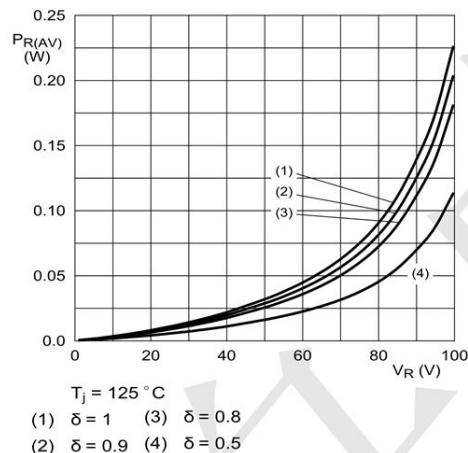
Fig 4. Reverse current as a function of reverse voltage; typical values

■ Typical Characteristics

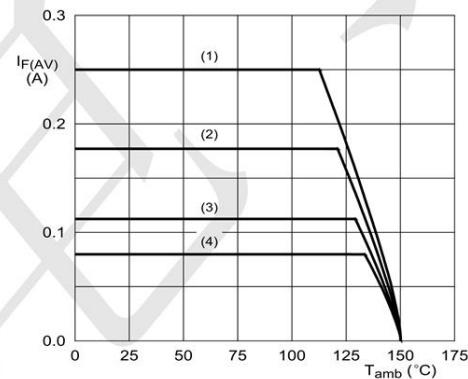


f = 1 MHz; T<sub>amb</sub> = 25 °C

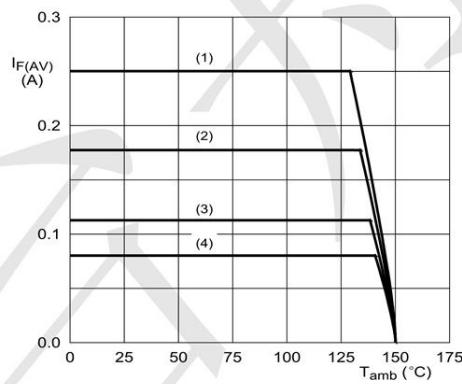
**Fig 5. Diode capacitance as a function of reverse voltage; typical values**



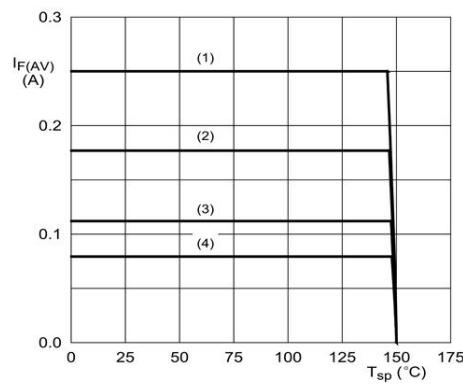
**Fig 6. Average reverse power dissipation as a function of reverse voltage; typical values**



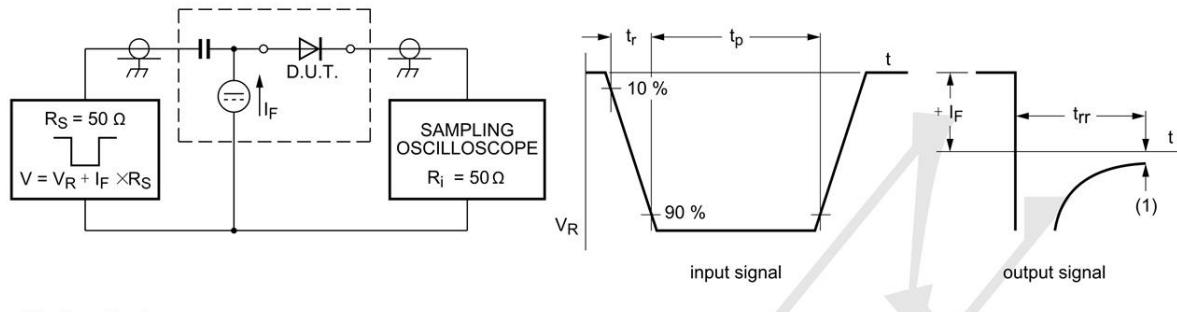
**Fig 7. Average forward current as a function of ambient temperature; typical values**



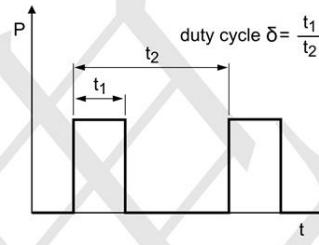
**Fig 8. Average forward current as a function of ambient temperature; typical values**



**Fig 9. Average forward current as a function of solder point temperature; typical values**



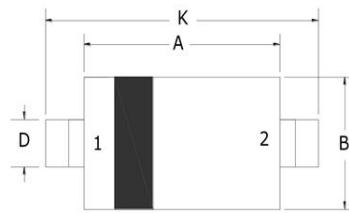
**Fig 10. Reverse recovery time test circuit and waveforms**



**Fig 11. Duty cycle definition**

The current ratings for the typical waveforms as shown in Figure 7, 8 and 9 are calculated according to the equations:  $I_{FAV} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

## Outline Drawing - SOD-323



Dim	Millimeters		Inches	
	Min	Max	Min	Max
<b>A</b>	1.60	1.80	0.063	0.071
<b>B</b>	1.2	1.40	0.047	0.055
<b>C</b>	0.80	0.90	0.031	0.035
<b>D</b>	0.25	0.35	0.010	0.014
<b>E</b>	0.15REF		0.006REF	
<b>H</b>	0	0.10	0	0.004
<b>J</b>	0.08	0.15	0.003	0.006
<b>K</b>	2.50	2.70	0.098	0.106

## Land Pattern - SOD-323

